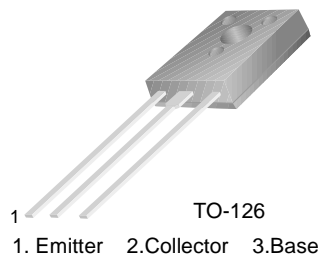


# KSC5026M

KSC5026M

## High Voltage and High Reliability

- High Speed Switching
- Wide SOA



## NPN Silicon Transistor

### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	1100	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	1.5	A
$I_{CP}$	Collector Current (Pulse)	5	A
$I_B$	Base Current	0.8	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}, I_E = 0$	1100			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	800			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}, I_C = 0$	7			V
$V_{CEX(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 0.75\text{A}$ $I_{B1} = -I_{B2} = 0.15\text{A}$ $L = 5\text{mH}$ , Clamped	800			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 800\text{V}, I_E = 0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			10	$\mu\text{A}$
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 0.1\text{A}$ $V_{CE} = 5\text{V}, I_C = 0.5\text{A}$	10 8		40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.75\text{A}, I_B = 0.15\text{A}$			2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 0.75\text{A}, I_B = 0.15\text{A}$			1.5	V
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		35		pF
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.1\text{A}$		15		MHz
$t_{ON}$	Turn On Time	$V_{CC} = 400\text{V}$ $I_C = 5I_{B1} = -2.5I_{B2} = 1\text{A}$ $R_L = 400\Omega$			0.5	$\mu\text{s}$
$t_{STG}$	Storage Time				3	$\mu\text{s}$
$t_F$	Fall Time				0.3	$\mu\text{s}$

## $h_{FE}$ Classification

Classification	N	R	O
$h_{FE1}$	10 ~ 20	15 ~ 30	20 ~ 40

# Typical Characteristics

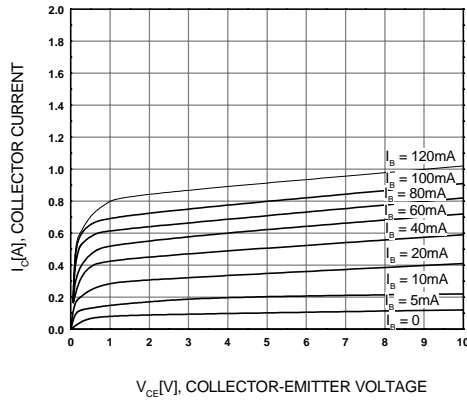


Figure 1. Static Characteristic

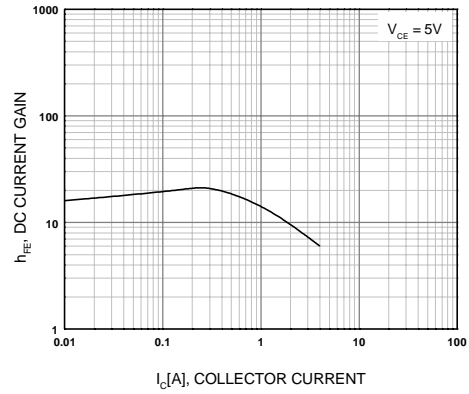


Figure 2. DC current Gain

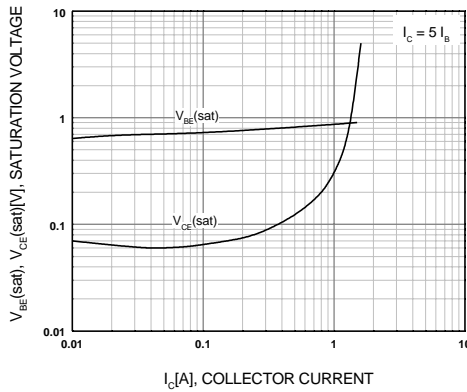


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

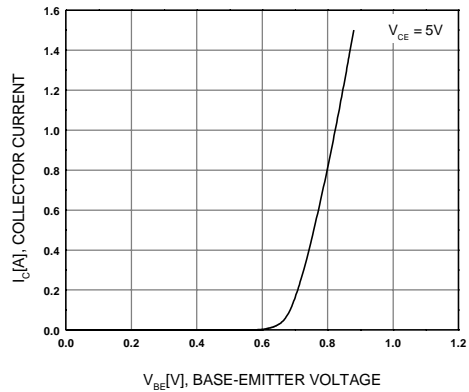


Figure 4. Base-Emitter On Voltage

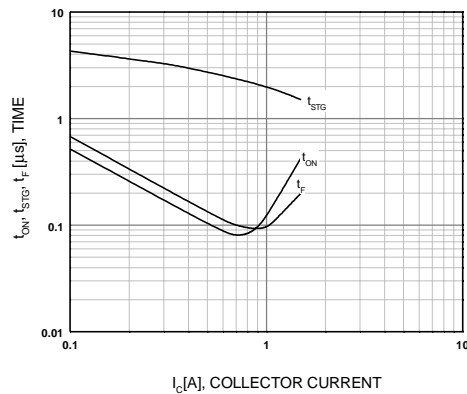


Figure 5. Switching Time

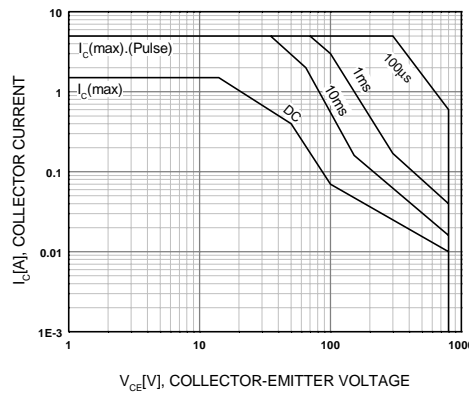


Figure 6. Safe Operating Area

## Typical Characteristics (Continued)

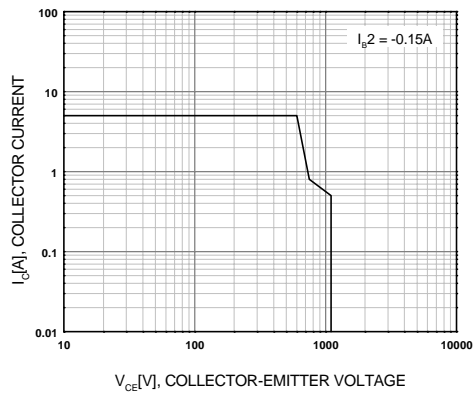


Figure 7. Reverse Bias Safe Operating Area

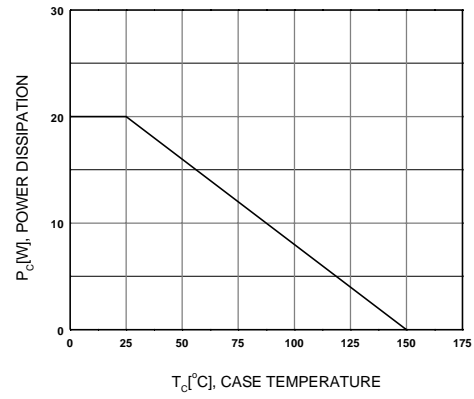


Figure 8. Power Derating

**KSC5026M**

Technical drawing of a 10-pin D-sub connector. The drawing includes a front view (top) and a side view (bottom).

**Front View Dimensions:**

- Width:  $8.00 \pm 0.30$
- Height:  $14.20 \text{ MAX}$
- Central feature diameter:  $3.90 \pm 0.10$
- Pin dimensions:  $0.75 \pm 0.10$ ,  $1.60 \pm 0.10$ ,  $0.75 \pm 0.10$
- Pin pitch:  $2.28 \text{ TYP}$  [ $2.28 \pm 0.20$ ]

**Side View Dimensions:**

- Height:  $11.00 \pm 0.20$
- Base width:  $3.25 \pm 0.20$
- Pin dimensions:  $0.50^{+0.10}_{-0.05}$ ,  $1.75 \pm 0.20$

**Labels:**

- 10-PIN D-SUB
- 2.28 TYP
- #1

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